

Itinerant Single Microwave Photon Detection

John Mark Kreikebaum¹, Kevin O'Brien², Baptiste Royer³, Arne Grimsmo⁴, Alexandre Blais³, Irfan Siddiqi¹ (PI)

¹Quantum Nanoelectronics Laboratory, University of California, Berkeley. ²Department of Electrical Engineering and Computer Science, Massachusetts Institute of Technology, ³Institut Quantique and Département de Physique, Université de Sherbrooke, ⁴Centre for Engineered Quantum Systems, School of Physics, The University of Sydney





Develop a high-fidelity detector for traveling single microwave photons which operates continuously without active reset or prior information about the photon's arrival time.

Optical photons, which can be detected with commercially available SPDs, have ~10⁴ times more energy than microwave photons, illustrated by the difference in area of the red and blue circles. Measuring single microwave photons is challenging due to their small energies compared to room temperature noise.

Detector theory



Using wQED to improve the toy model

If slight detunings between the absorbers are introduced, coherent exchange between the bright and dark state occurs allowing for photons to be trapped $|D\rangle$ for longer than the inverse of the detector's absorption bandwidth.

Actual

6394

0.775

5600

2.8

0.11-0.15



Readout resonator Waveguide with $\lambda/2$ spacing between absorbers $\hat{H}_{\chi}^{D} = g_z \hat{N}_B \hat{X}_A + \sum \Delta_i \hat{b}_i^{\dagger} \hat{b}_i + 2\chi \hat{N}_B \hat{a}^{\dagger} \hat{a} + \Delta_+ \hat{b}_+^{\dagger} \hat{b}_+$ i=1

RF design and fabrication





8:1 asymmetric squids were used to provide tunable non-linear inductance with reduced susceptibility to flux noise¹. Shunting this squid with a capacitor forms a transmon qubit. ¹Hutchings et al. PRA 8,044003 (2017) Single photon detector (SPD) v4 currently under test at UCB

Processing details: 6" wafer yields 64 devices in 3 days.

- Design layout with GDS-py
- Clean high resistivity intrinsic Si with piranha and BOE
- Sputter 200 nm Nb, spin MMA, e-beam pattern Nb features - Develop (3:1 IPA:MIBK)
- ICP-RIE etch Nb (BCl₃/Cl₂), strip resist (NMP)
- HF clean, spin e-beam resist bilayer (MMA/AR-P 6200.9)
- E-beam write Manhattan style junctions
- Cold develop AR-P with NAA
- Develop MMA with ultrasonically assisted 3:1 IPA:H₂O
- Al evap, in situ oxidation, Al evap, liftoff
- Spin, write junction contact pieces
- Ion mill, normal angle AI evap, liftoff
- Probe junction resistances, dice
- Post-process cleaning, wire bond

Josephson junction uniformity

The next generation SPD (shown at right) will require thousands of Josephson junctions to operate. Although simulations show that the detector will work in the presence of moderate disorder (~ 10%), minimizing global variations will lead to higher yield and benefit concurrent fabrication efforts of ever-larger quantum processors. Results below are on test wafers containing 3000 ~ 200 x 200 nm junctions after 34 iterations of improvements.





Simplified circuit diagram of the mixing chamber RF components. The output of the SPD is connected with Nb-Ti coax to a phase-sensitive JPA acting as a low noise preamplifier before a Josephson Traveling Wave Parametric Amplifier (JTWPA) since it has, combined with its required microwave components, ~ 3 dB of insertion loss.



Outlook: next generation SPD



Theory: The ensemble of absorbers in SPDv4 is replaced with a metamaterial transmission line referred to as a composite right/left-handed (CRLH) transmission line which is attractive due to its potential for dispersion and band-structure engineering. For a specific choice of parameters, you get an upper and lower frequency cutoff (good for limiting dark counts and readout resonator decay!), frequency independent characteristic impedance, and slow light propagation. Distributed coupling and long physical length of the detector (>>1 wavelength) limits information gathered about the photon's position to minimize momentum backaction. A klopfenstein impedance transformer directs photons into the device with minimal loss from conventional 50 Ω microwave hardware.

